

# Yong Tae Kim

## List of Publications by Year in descending order

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31  
papers

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citations

1163117

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31  
docs citations

31  
times ranked

289  
citing authors

#	ARTICLE	IF	CITATIONS
1	Memory Operation of Z <sup>2</sup> -FET Without Selector at High Temperature. IEEE Journal of the Electron Devices Society, 2021, 9, 658-662.	2.1	2
2	Improved Retention Characteristics of Z <sup>2</sup> -FET Employing Half Back-Gate Control. IEEE Transactions on Electron Devices, 2021, 68, 1041-1044.	3.0	2
3	Memory Operations of Zero Impact Ionization, Zero Subthreshold Swing FET Matrix Without Selectors. IEEE Electron Device Letters, 2020, 41, 361-364.	3.9	4
4	Understanding of relationship between dopant and substitutional site to develop novel phase-change materials based on In <sub>3</sub> SbTe <sub>2</sub> . Japanese Journal of Applied Physics, 2019, 58, SBBB02.	1.5	15
5	Material design for Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> phase-change material with thermal stability and lattice distortion. Scripta Materialia, 2019, 170, 16-19.	5.2	7
6	Characteristics of band modulation FET on sub 10 nm SOI. Japanese Journal of Applied Physics, 2019, 58, SBBB07.	1.5	2
7	Interface-Driven Phase Transition of Phase-Change Material. Crystal Growth and Design, 2019, 19, 2123-2130.	3.0	5
8	A review of the Z <sup>2</sup> -FET 1T-DRAM memory: Operation mechanisms and key parameters. Solid-State Electronics, 2018, 143, 10-19.	1.4	36
9	Effects of Y Dopant on Lattice Distortion and Electrical Properties of In <sub>3</sub> SbTe <sub>2</sub> Phase-Change Material. Physica Status Solidi - Rapid Research Letters, 2017, 11, 1700275.	2.4	6
10	Effects of Y Dopant on Lattice Distortion and Electrical Properties of In <sub>3</sub> SbTe <sub>2</sub> Phase-Change Material (Phys. Status Solidi RRL 11/2017). Physica Status Solidi - Rapid Research Letters, 2017, 11, 1770356.	2.4	0
11	Effects of an in vacancy on local distortion of fast phase transition in Bi-doped In <sub>3</sub> SbTe <sub>2</sub> . Journal of the Korean Physical Society, 2017, 71, 946-949.	0.7	1
12	The low temperature epitaxy of Ge on Si (1 0 0) substrate using two different precursors of GeH <sub>4</sub> and Ge <sub>2</sub> H <sub>6</sub> . Solid-State Electronics, 2016, 124, 35-41.	1.4	6
13	Lattice Distortion in In <sub>3</sub> SbTe <sub>2</sub> Phase Change Material with Substitutional Bi. Scientific Reports, 2015, 5, 12867.	3.3	17
14	The effect of carbon-doped In <sub>3</sub> Sb <sub>1</sub> Te <sub>2</sub> ternary alloys for multibit (MLC) phase-change memory. Physica Status Solidi - Rapid Research Letters, 2014, 8, 243-247.	2.4	6
15	Microstructural failure in Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> phase change memory cell. Physica Status Solidi (B): Basic Research, 2014, 251, 435-438.	1.5	7
16	Atomic crystal structure of ordered In <sub>3</sub> Sb <sub>1</sub> Te <sub>2</sub> ternary alloy studied by high-resolution transmission electron microscopy. Applied Physics Letters, 2012, 100, .	3.3	11
17	Microstructures corresponding to multilevel resistances of In <sub>3</sub> Sb <sub>1</sub> Te <sub>2</sub> phase-change memory. Applied Physics Letters, 2011, 98, 091915.	3.3	24
18	Nucleation, growth, and phase transformation mechanism of Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> thin films. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 2542-2545.	1.8	3

#	ARTICLE	IF	CITATIONS
19	Investigation of electrical characteristics of the $\text{In}_{3}\text{Sb}_{1}\text{Te}_{2}$ ternary alloy for application in phase-change memory. <i>Physica Status Solidi - Rapid Research Letters</i> , 2009, 3, 103-105.	2.4	62
20	Mechanism of shear transformation in $\text{GeBiTe}$ alloys. <i>Physica Status Solidi - Rapid Research Letters</i> , 2009, 3, 254-256.	2.4	4
21	Effects of excess Sb on crystallization of $\text{In}$ -phase $\text{SbTe}$ binary thin films. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008, 205, 1636-1640.	1.8	24
22	Influences of partial melting and overheating on amorphization of $\text{Ge}_{2}\text{Sb}_{2}\text{Te}_{5}$ during the reset process. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008, 205, 2657-2661.	1.8	0
23	Investigation of the structural transformation behavior of $\text{Ge}_{2}\text{Sb}_{2}\text{Te}_{5}$ thin films using high resolution electron microscopy. <i>Applied Physics Letters</i> , 2007, 91, 101909.	3.3	22
24	Structural study on the crystallization behavior of $\text{Sb}_{3}\text{Te}_{2}$ alloy for phase change memory. <i>Physica Status Solidi - Rapid Research Letters</i> , 2007, 1, R25-R27.	2.4	7
25	Pulse plasma assisted atomic layer deposition of $\text{W-C-N}$ thin films for Cu interconnects. <i>Physica Status Solidi A</i> , 2005, 202, R164-R166.	1.7	8
26	Improvement of ferroelectric properties of $\text{Pt/SrBi}_{2}\text{Nb}_{2}\text{O}_{9}/\text{SiO}_{2}/\text{Si}$ gate structure through oxygen plasma rapid thermal annealing. <i>Physica Status Solidi A</i> , 2004, 201, 125-129.	1.7	1
27	Equivalent circuit model for the electrical analysis of a spin bipolar transistor. <i>Physica Status Solidi A</i> , 2004, 201, 808-814.	1.7	0
28	Fabrication of MFISFETs with $\text{Pt/SrBi}_{2}\text{Ta}_{2}\text{O}_{9}/\text{Y}_{2}\text{O}_{3}/\text{Si}$ gate structure by developing an etch-stop process. <i>Physica Status Solidi A</i> , 2004, 201, R65-R68.	1.7	2
29	A new atomic layer deposition of $\text{W-N}$ thin films. <i>Physica Status Solidi A</i> , 2004, 201, R92-R95.	1.7	5
30	Lattice structural analysis of hydrogen induced defects in $\text{SrBi}_{2}\text{Nb}_{2}\text{O}_{9}$ thin films. <i>Physica Status Solidi A</i> , 2004, 201, R123-R126.	1.7	0
31	Characteristics of plasma enhanced chemical vapor deposited $\text{W-B-N}$ thin films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2002, 20, 194-197.	2.1	5